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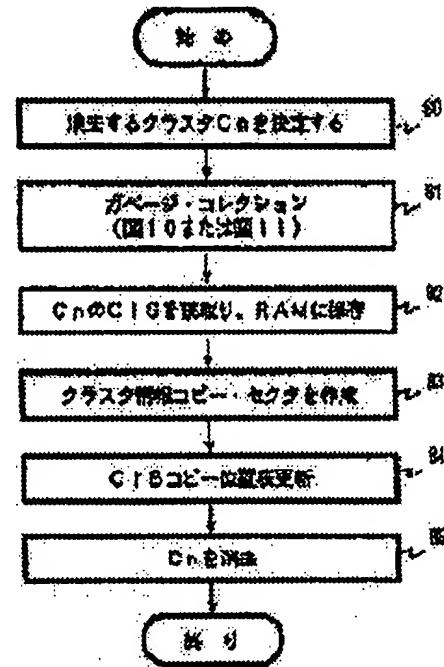
(21)Application number : 05-050247 (71)Applicant : INTERNATL BUSINESS MACH CORP <IBM>  
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## (54) BATCH ERASURE TYPE NON-VOLATILE MEMORY

## (57)Abstract:

PURPOSE: To enhance resistance against fault like power cutoff, etc., in a semiconductor disk device which uses a batch erasure type non-volatile memory.

CONSTITUTION: A batch erasure type non-volatile memory contains plural sectors and attribute information for recognizing their own attribute is written in every sector. As a rule, a cluster information sector is placed at the front position of a cluster to which it belongs. Then, data sector is placed in a data area which is an area except the front position of a cluster. A controller connected to the memory produces a cluster information copy sector in a data area at the time of cluster erasure, reconstitutes cluster management information from the cluster information copy sector and produces a cluster information sector at the time of cluster initialization.



## LEGAL STATUS

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